

*Sub 2*

*a3*

7. (Amended) A method for forming a crystalline semiconductor film at a desired position on a substrate, comprising the steps of:

- a) preparing the substrate having an amorphous semiconductor film formed thereon;
- b) preparing an optical mask having a predetermined pattern;
- c) relatively positioning a projection area of the optical mask at the desired position on the substrate;
- d) irradiating the desired position of the amorphous semiconductor film with laser light through the optical mask to change an irradiated portion of the amorphous semiconductor film to the crystalline semiconductor film; and
- e) forming an insulation film on the crystalline semiconductor film and the amorphous semiconductor film.

#### REMARKS

An Office Action was mailed on October 31, 2001. Claims 1-14 are pending in the present application, claims 11-14 having been withdrawn from consideration. With this response, amendments are made to the specification and to pending claims 1 and 7. The amendment to the specification simply identifies reference numerals in Figure 1 with an existing textual description at page 3, lines 12 – 23. No new matter is introduced.